L660N-06

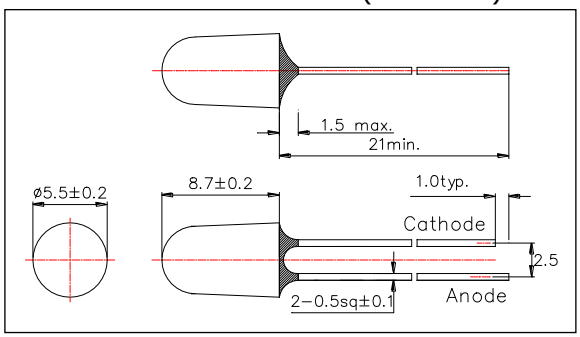
For Plant Growth / Photo Synthetically Active Radiation Use

L660N-06 is an AlGaInP LED mounted on a lead frame with a clear epoxy lens.
This is designed for the highest Po and damp proof.
On forward bias, it emits a band of visible light that peaks 660nm.

<Specifications>

1. Product Name: Red LED Lamp
2. Type Number: L660N-06
3. Chip:
   - Chip material: AlGaInP
   - Peak Wavelength: 660nm type
4. Package
   - Type: Φ5mm Clear Molding
   - Resin Material: Epoxy Resin
   - Lead Frame: Soldered(Lead Free)

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25℃]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	120	mW
Forward Current	IF	50	mA
Pulse Forward Current*	IFP	-	mA
Reverse Voltage	VR	5	V
Junction Temperature	Tj	100	℃
Thermal Resistance**	Rthjp	190	K/W
Operating Temperature	TOPR	-40 ~ +80	℃
Storage Temperature	TSTG	-40 ~ +100	℃
Soldering Temperature***	TSOL	265	℃

* Duty=1% and Pulse Width=10us.
** Junction - ambient, leads 7mm, soldered on PCB.
*** Soldering condition must be completed within 3 second at 265℃.

Electro-Optical Characteristics [Ta=25℃]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=20mA		2.1	2.3	V
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power*	PO	IF=20mA	10	15		mW
Radiant Intensity	IE	IF=20mA		120		mW/sr
Brightness**	IV	IF=20mA		13,000		mcd
Peak Wavelength	λP	IF=20mA	650	660	670	nm
Half Width	Δλ	IF=20mA		18		nm
Viewing Half Angle	θ1/2	IF=20mA		±3		deg

* Measured by Photodyne #500
** Measured by Tektronix J-16

RoHS Compliant